Eduardo Alves

List of Publications by Year
in descending order

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		34016	69108
785	13,721	52	77
papers	citations	h-index	g-index

794	794	794	10761
all docs	docs citations	times ranked	citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of post-annealing on the properties of copper oxide thin films obtained from the oxidation of evaporated metallic copper. Applied Surface Science, 2008, 254, 3949-3954.	3.1	226
2	Strain and composition distributions in wurtzite InGaN/GaN layers extracted from x-ray reciprocal space mapping. Applied Physics Letters, 2002, 80, 3913-3915.	1.5	209
3	Characterisation of Ti1â^'xSixNy nanocomposite films. Surface and Coatings Technology, 2000, 133-134, 307-313.	2.2	190
4	Compositional pulling effects inInxGa1â^'xN/GaNlayers:â€ƒA combined depth-resolved cathodoluminescence and Rutherford backscattering/channeling study. Physical Review B, 2001, 64, .	1.1	176
5	Structural, optical and mechanical properties of coloured TiNxOy thin films. Thin Solid Films, 2004, 447-448, 449-454.	0.8	169
6	Overview of the JET results in support to ITER. Nuclear Fusion, 2017, 57, 102001.	1.6	150
7	Influence of nitrogen content on the structural, mechanical and electrical properties of TiN thin films. Surface and Coatings Technology, 2005, 191, 317-323.	2.2	146
8	Microstructure and mechanical properties of nanocomposite (Ti,Si,Al)N coatings. Thin Solid Films, 2001, 398-399, 391-396.	0.8	131
9	Anomalous Ion Channeling inAlInN/GaNBilayers: Determination of the Strain State. Physical Review Letters, 2006, 97, 085501.	2.9	125
10	Metal-organic vapor phase epitaxy and properties of AlInN in the whole compositional range. Applied Physics Letters, 2007, 90, 022105.	1.5	119
11	Materials design data for reduced activation martensitic steel type EUROFER. Journal of Nuclear Materials, 2004, 329-333, 257-262.	1.3	118
12	Hard nanocomposite Tiâ€"Siâ€"N coatings prepared by DC reactive magnetron sputtering. Surface and Coatings Technology, 2000, 133-134, 234-239.	2.2	115
13	Compositional dependence of the strain-free optical band gap in InxGa1â^'xN layers. Applied Physics Letters, 2001, 78, 2137-2139.	1.5	104
14	Damage formation and annealing at low temperatures in ion implanted ZnO. Applied Physics Letters, 2005, 87, 191904.	1.5	100
15	Structural and optical properties of InGaN/GaN layers close to the critical layer thickness. Applied Physics Letters, 2002, 81, 1207-1209.	1.5	94
16	Photoluminescence and lattice location of Eu and Pr implanted GaN samples. Physica B: Condensed Matter, 2001, 308-310, 22-25.	1.3	91
17	Identification of the prime optical center in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaN</mml:mtext><mml:mo>:</mml:mo><mml:msup><mml:mrow><mml:mtext>Eu</mm Physical Review B, 2010, 81, .	1.1	90
18	Structural, electrical, optical, and mechanical characterizations of decorative ZrOxNy thin films. Journal of Applied Physics, 2005, 98, 023715.	1.1	87

#	ARTICLE	IF	CITATIONS
19	Overview of the JET preparation for deuteriumâ€"tritium operation with the ITER like-wall. Nuclear Fusion, 2019, 59, 112021.	1.6	87
20	Direct Evidence for As as a Zn-Site Impurity in ZnO. Physical Review Letters, 2005, 95, 215503.	2.9	86
21	Selectively excited photoluminescence from Eu-implanted GaN. Applied Physics Letters, 2005, 87, 112107.	1.5	85
22	Photoluminescence studies in ZnO samples. Physica B: Condensed Matter, 2001, 308-310, 985-988.	1.3	84
23	Effects of ion bombardment on properties of d.c. sputtered superhard (Ti, Si, Al)N nanocomposite coatings. Surface and Coatings Technology, 2002, 151-152, 515-520.	2.2	81
24	Synthesis, surface modification and optical properties of Tb3+-doped ZnO nanocrystals. Nanotechnology, 2006, 17, 834-839.	1.3	75
25	Material migration patterns and overview of first surface analysis of the JET ITER-like wall. Physica Scripta, 2014, T159, 014010.	1.2	75
26	Plasmaâ€"wall interaction studies within the EUROfusion consortium: progress on plasma-facing components development and qualification. Nuclear Fusion, 2017, 57, 116041.	1.6	75
27	Preparation of magnetron sputtered TiNxOy thin films. Surface and Coatings Technology, 2003, 174-175, 197-203.	2.2	74
28	Tuning of the surface plasmon resonance in TiO2/Au thin films grown by magnetron sputtering: The effect of thermal annealing. Journal of Applied Physics, 2011, 109, .	1.1	74
29	Implantation damage formation in a-, c- and m-plane GaN. Acta Materialia, 2017, 123, 177-187.	3.8	73
30	Three-step amorphisation process in ion-implanted GaN at 15 K. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 1028-1032.	0.6	71
31	Characterization of TiAlSiN/TiAlSiON/SiO2 optical stack designed by modelling calculations for solar selective applications. Solar Energy Materials and Solar Cells, 2012, 105, 202-207.	3.0	70
32	Solar selective absorbers based on Al2O3:W cermets and AlSiN/AlSiON layers. Solar Energy Materials and Solar Cells, 2015, 137, 93-100.	3.0	68
33	High-temperature annealing and optical activation of Eu-implanted GaN. Applied Physics Letters, 2004, 85, 2712-2714.	1.5	67
34	Electrical, structural and optical characterization of copper oxide thin films as a function of post annealing temperature. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2143-2148.	0.8	67
35	Lattice site location and optical activity of Er implanted ZnO. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 1047-1051.	0.6	66
36	Influence of the chemical and electronic structure on the electrical behavior of zirconium oxynitride films. Journal of Applied Physics, 2008, 103, .	1.1	66

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37	High Orbital Angular Momentum Harmonic Generation. Physical Review Letters, 2016, 117, 265001.	2.9	66
38	Micron-scale analysis of SiC/SiCf composites using the new Lisbon nuclear microprobe. Nuclear Instruments & Methods in Physics Research B, 2000, 161-163, 334-338.	0.6	65
39	Property change in ZrNxOy thin films: effect of the oxygen fraction and bias voltage. Thin Solid Films, 2004, 469-470, 11-17.	0.8	65
40	Efficient dipole-dipole coupling of Mott-Wannier and Frenkel excitons in (Ga,In)N quantum well/polyfluorene semiconductor heterostructures. Physical Review B, 2007, 76, .	1.1	64
41	Radiation damage in ZnO ion implanted at 15K. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 2708-2711.	0.6	64
42	Role of Nanoscale Strain Inhomogeneity on the Light Emission from InGaN Epilayers. Advanced Functional Materials, 2007, 17, 37-42.	7.8	60
43	Identification of donor-related impurities in ZnO using photoluminescence and radiotracer techniques. Physical Review B, 2006, 73, .	1.1	59
44	An overview of the comprehensive First Mirror Test in JET with ITER-like wall. Physica Scripta, 2014, T159, 014011.	1.2	59
45	Dielectric function of nanocrystalline silicon with few nanometers (<3 nm) grain size. Applied Physics Letters, 2003, 82, 2993-2995.	1.5	58
46	Application of RZ-scan technique for investigation of nonlinear refraction of sapphire doped with Ag, Cu, and Au nanoparticles. Optics Communications, 2005, 253, 205-213.	1.0	58
47	Transmission electron microscopy investigation of the structural damage formed in GaN by medium range energy rare earth ion implantation. Journal of Applied Physics, 2006, 100, 073520.	1.1	58
48	Optical energies of AlInN epilayers. Journal of Applied Physics, 2008, 103, .	1.1	58
49	Photoluminescence and damage recovery studies in Fe-implanted ZnO single crystals. Journal of Applied Physics, 2003, 93, 8995-9000.	1.1	56
50	Interpretation of double x-ray diffraction peaks from InGaN layers. Applied Physics Letters, 2001, 79, 1432-1434.	1.5	55
51	Implantation site of rare earths in single-crystalline ZnO. Applied Physics Letters, 2003, 82, 1173-1175.	1.5	55
52	Near-band-edge slow luminescence in nominally undoped bulk ZnO. Journal of Applied Physics, 2005, 98, 013502.	1.1	54
53	Radiation damage formation and annealing in GaN and ZnO. Proceedings of SPIE, 2011, , .	0.8	54
54	Optimization of nanocomposite Au/TiO 2 thin films towards LSPR optical-sensing. Applied Surface Science, 2018, 438, 74-83.	3.1	54

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55	Ion beam analysis of fusion plasma-facing materials and components: facilities and research challenges. Nuclear Fusion, 2020, 60, 025001.	1.6	54
56	Raman study of the A1(LO) phonon in relaxed and pseudomorphic InGaN epilayers. Applied Physics Letters, 2003, 83, 4761-4763.	1.5	53
57	Optical studies of ZnO nanocrystals doped with Eu3+ ions. Applied Physics A: Materials Science and Processing, 2007, 88, 129-133.	1.1	53
58	Corrosion resistance of ZrNxOy thin films obtained by rf reactive magnetron sputtering. Thin Solid Films, 2004, 469-470, 274-281.	0.8	52
59	Microstructure of (Ti,Si,Al)N nanocomposite coatings. Surface and Coatings Technology, 2004, 177-178, 369-375.	2.2	52
60	High Mobility a-IGO Films Produced at Room Temperature and Their Application in TFTs. Electrochemical and Solid-State Letters, 2010, 13, H20.	2.2	52
61	Identifying the influence of the intrinsic defects in Gd-doped ZnO thin-films. Journal of Applied Physics, 2016, 119, .	1.1	52
62	Long-term fuel retention in JET ITER-like wall. Physica Scripta, 2016, T167, 014075.	1.2	52
63	Overview of JET results for optimising ITER operation. Nuclear Fusion, 2022, 62, 042026.	1.6	52
64	Lattice location and thermal stability of implanted Fe in ZnO. Applied Physics Letters, 2004, 85, 4899-4901.	1.5	50
65	Relaxation of compressively strained AlInN on GaN. Journal of Crystal Growth, 2008, 310, 4058-4064.	0.7	50
66	Fuel retention in JET ITER-Like Wall from post-mortem analysis. Journal of Nuclear Materials, 2015, 463, 961-965.	1.3	50
67	The influence of annealing treatments on the properties of Ag:TiO2 nanocomposite films prepared by magnetron sputtering. Applied Surface Science, 2012, 258, 4028-4034.	3.1	49
68	Transparent thin film transistors based on indium oxide semiconductor. Journal of Non-Crystalline Solids, 2006, 352, 2311-2314.	1.5	48
69	PVD-Grown photocatalytic TiO2 thin films on PVDF substrates for sensors and actuators applications. Thin Solid Films, 2008, 517, 1161-1166.	0.8	48
70	Structural and optical characterization of Eu-implanted GaN. Journal Physics D: Applied Physics, 2009, 42, 165103.	1.3	48
71	Global erosion and deposition patterns in JET with the ITER-like wall. Journal of Nuclear Materials, 2015, 463, 157-161.	1.3	48
72	High temperature annealing of rare earth implanted GaN films: Structural and optical properties. Optical Materials, 2006, 28, 750-758.	1.7	47

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73	Overview of fuel inventory in JET with the ITER-like wall. Nuclear Fusion, 2017, 57, 086045.	1.6	47
74	Structural evolution in ZrNxOy thin films as a function of temperature. Surface and Coatings Technology, 2006, 200, 2917-2922.	2.2	46
75	Overview of the JET ITER-like wall divertor. Nuclear Materials and Energy, 2017, 12, 499-505.	0.6	46
76	Elastic properties of (Ti,Al,Si)N nanocomposite films. Surface and Coatings Technology, 2001, 142-144, 110-116.	2.2	45
77	Hydrogenated silicon carbon nitride films obtained by HWCVD, PA-HWCVD and PECVD techniques. Journal of Non-Crystalline Solids, 2006, 352, 1361-1366.	1.5	45
78	Direct observation of mono-vacancy and self-interstitial recovery in tungsten. APL Materials, 2019, 7, .	2.2	45
79	Lattice location and optical activation of rare earth implanted GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 132-140.	1.7	44
80	Mechanical characterization of reactively magnetron-sputtered TiN films. Surface and Coatings Technology, 2003, 174-175, 375-382.	2.2	44
81	Functional and optical properties of Au:TiO2 nanocomposite films: The influence of thermal annealing. Applied Surface Science, 2010, 256, 6536-6542.	3.1	43
82	Room-temperature growth of crystalline indium tin oxide films on glass using low-energy oxygen-ion-beam assisted deposition. Journal of Applied Physics, 2003, 93, 2262-2266.	1.1	42
83	Free electron behavior in InN: On the role of dislocations and surface electron accumulation. Applied Physics Letters, 2009, 94, 022109.	1.5	41
84	Lattice location and stability of implanted Cu in ZnO. Physical Review B, 2004, 69, .	1.1	40
85	The role of composition, morphology and crystalline structure in the electrochemical behaviour of TiNx thin films for dry electrode sensor materials. Electrochimica Acta, 2009, 55, 59-67.	2.6	40
86	Optical and structural analysis of solar selective absorbing coatings based on AlSiOx:W cermets. Solar Energy, 2017, 150, 335-344.	2.9	40
87	Cathodoluminescence of rare earth implanted Ga2O3and GeO2nanostructures. Nanotechnology, 2011, 22, 285706.	1.3	39
88	Mechanisms of damage formation in Eu-implanted GaN probed by X-ray diffraction. Europhysics Letters, 2011, 96, 46002.	0.7	39
89	Efficient temperature sensing using photoluminescence of Er/Yb implanted GaN thin films. Sensors and Actuators B: Chemical, 2017, 248, 769-776.	4.0	39
90	Structural and corrosion behaviour of stoichiometric and substoichiometric TiN thin films. Surface and Coatings Technology, 2004, 180-181, 158-163.	2.2	38

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91	Raman spectra and structural analysis in ZrOxNy thin films. Thin Solid Films, 2006, 515, 1132-1137.	0.8	38
92	Optically active centers in Eu implanted, Euin situdoped GaN, and Eu doped GaN quantum dots. Journal of Applied Physics, 2009, 105, 043104.	1.1	38
93	Optical doping and damage formation in AlN by Eu implantation. Journal of Applied Physics, 2010, 107, 023525.	1.1	38
94	Nanocomposite Ag:TiN thin films for dry biopotential electrodes. Applied Surface Science, 2013, 285, 40-48.	3.1	38
95	Structural and luminescence properties of Eu and Er implanted Bi2O3 nanowires for optoelectronic applications. Journal of Materials Chemistry C, 2013, 1, 7920.	2.7	38
96	A design of selective solar absorber for high temperature applications. Solar Energy, 2018, 172, 177-183.	2.9	38
97	Enhancement in the photocatalytic nature of nitrogen-doped PVD-grown titanium dioxide thin films. Journal of Applied Physics, 2009, 106, .	1.1	37
98	TiNx coated polycarbonate for bio-electrode applications. Corrosion Science, 2012, 56, 49-57.	3.0	37
99	Ion beam studies of TiNxOy thin films deposited by reactive magnetron sputtering. Surface and Coatings Technology, 2004, 180-181, 372-376.	2.2	36
100	Characterization of hard DC-sputtered Si-based TiN coatings: the effect of composition and ion bombardment. Surface and Coatings Technology, 2004, 188-189, 351-357.	2.2	36
101	Structural evolution of Tiâ€"Alâ€"Siâ€"N nanocomposite coatings. Vacuum, 2009, 83, 1206-1212.	1.6	36
102	Hydrogen in InN: A ubiquitous phenomenon in molecular beam epitaxy grown material. Applied Physics Letters, 2010, 96, .	1.5	36
103	High In-content InGaN layers synthesized by plasma-assisted molecular-beam epitaxy: Growth conditions, strain relaxation, and In incorporation kinetics. Journal of Applied Physics, 2014, 116, .	1.1	36
104	Surface analysis of tiles and samples exposed to the first JET campaigns with the ITER-like wall. Physica Scripta, 2014, T159, 014012.	1.2	35
105	Neutron spectroscopy measurements of 14 MeV neutrons at unprecedented energy resolution and implications for deuteriumâ€"tritium fusion plasma diagnostics. Measurement Science and Technology, 2018, 29, 045502.	1.4	35
106	Green, red and infrared Er-related emission in implanted GaN:Er and GaN:Er,O samples. Journal of Applied Physics, 2001, 89, 6183-6188.	1.1	34
107	TiAgx thin films for lower limb prosthesis pressure sensors: Effect of composition and structural changes on the electrical and thermal response of the films. Applied Surface Science, 2013, 285, 10-18.	3.1	34
108	p-Type <formula formulatype="inline"><tex Notation="TeX">${hbox{Cu}}_{x}{hbox{O}}$</tex> </formula> Thin-Film Transistors Produced by Thermal Oxidation. Journal of Display Technology, 2013, 9, 735-740.	1.3	34

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109	Comparison of low- and room-temperature damage formation in Ar ion implanted GaN and ZnO. Nuclear Instruments & Methods in Physics Research B, 2013, 307, 394-398.	0.6	34
110	OPTICAL DOPING OF NITRIDES BY ION IMPLANTATION. Modern Physics Letters B, 2001, 15, 1281-1287.	1.0	33
111	Depth-resolved analysis of spontaneous phase separation in the growth of lattice-matched AlInN. Journal Physics D: Applied Physics, 2010, 43, 055406.	1.3	33
112	Rapid thermal annealing of rare earth implanted ZnO epitaxial layers. Optical Materials, 2011, 33, 1139-1142.	1.7	33
113	Properties of tantalum oxynitride thin films produced by magnetron sputtering: The influence of processing parameters. Vacuum, 2013, 98, 63-69.	1.6	33
114	Mechanisms of Implantation Damage Formation in Al_{<i>x</i>}Ga_{1â€"<i>x</i>}N Compounds. Journal of Physical Chemistry C, 2016, 120, 7277-7283.	1.5	33
115	Tribocorrosion behaviour of ZrOxNy thin films for decorative applications. Surface and Coatings Technology, 2006, 200, 6634-6639.	2.2	32
116	Deuterium retention in tin (Sn) and lithiumâ€"tin (Liâ€"Sn) samples exposed to ISTTOK plasmas. Nuclear Materials and Energy, 2017, 12, 709-713.	0.6	32
117	Luminescence of Eu ions in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> the entire alloy composition range. Physical Review B, 2009, 80, .	1.1	31
118	Consolidation of Wâ€"Ta composites: Hot isostatic pressing and spark and pulse plasma sintering. Fusion Engineering and Design, 2015, 98-99, 1950-1955.	1.0	31
119	Substrate effect on CdTe layers grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 1997, 70, 1314-1316.	1.5	30
120	Optical doping of ZnO with Tm by ion implantation. Physica B: Condensed Matter, 2003, 340-342, 235-239.	1.3	30
121	Roughness in GaN/InGaN films and multilayers determined with Rutherford backscattering. Nuclear Instruments & Methods in Physics Research B, 2004, 217, 479-497.	0.6	30
122	First results and surface analysis strategy for plasma-facing components after JET operation with the ITER-like wall. Physica Scripta, 2014, T159, 014016.	1.2	30
123	Electrochemical behaviour of nanocomposite Agx:TiN thin films for dry biopotential electrodes. Electrochimica Acta, 2014, 125, 48-57.	2.6	30
124	Thin films of Agâ€"Au nanoparticles dispersed in TiO₂: influence of composition and microstructure on the LSPR and SERS responses. Journal Physics D: Applied Physics, 2018, 51, 205102.	1.3	30
125	Effect of annealing temperature on luminescence in Eu implanted GaN. Optical Materials, 2006, 28, 780-784.	1.7	29
126	Visible and infrared luminescence study of Er doped Î²-Ga₂O₃and Er₃Ga₅O₁₂. Journal Physics D: Applied Physics, 2008, 41, 065406.	1.3	29

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127	Lattice site location of optical centers in GaN:Eu light emitting diode material grown by organometallic vapor phase epitaxy. Applied Physics Letters, 2010, 97, 111911.	1.5	29
128	Single phase a-plane MgZnO epilayers for UV optoelectronics: substitutional behaviour of Mg at large contents. CrystEngComm, 2012, 14, 1637-1640.	1.3	29
129	Study of the relationship between crystal structure and luminescence in rare-earth-implanted Ga2O3 nanowires during annealing treatments. Journal of Materials Science, 2014, 49, 1279-1285.	1.7	29
130	Utilization of native oxygen in Eu(RE)-doped GaN for enabling device compatibility in optoelectronic applications. Scientific Reports, 2016, 6, 18808.	1.6	29
131	Incorporation and stability of erbium in sapphire by ion implantation. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 429-432.	0.6	28
132	Comparative study of radiation damage in GaN and InGaN by 400 keV Au implantation. Nuclear Instruments & Methods in Physics Research B, 2004, 218, 36-41.	0.6	28
133	Tribological behaviour of Cl-implanted TiN coatings for biomedical applications. Wear, 2007, 262, 1337-1345.	1.5	28
134	Influence of the O/C ratio in the behaviour of TiCxOy thin films. Surface and Coatings Technology, 2007, 201, 5587-5591.	2.2	28
135	Optical properties of LFZ grown Î²-Ga2O3:Eu3+ fibres. Applied Surface Science, 2012, 258, 9157-9161.	3.1	28
136	Intense luminescence emission from rare-earth-doped MoO3nanoplates and lamellar crystals for optoelectronic applications. Journal Physics D: Applied Physics, 2014, 47, 355105.	1.3	28
137	Assessment of erosion, deposition and fuel retention in the JET-ILW divertor from ion beam analysis data. Nuclear Materials and Energy, 2017, 12, 559-563.	0.6	28
138	Amorphisation of GaN during processing with rare earth ion beams. Superlattices and Microstructures, 2004, 36, 737-745.	1.4	27
139	Structural stability of decorative ZrNxOy thin films. Surface and Coatings Technology, 2005, 200, 748-752.	2.2	27
140	Defect production in neutron irradiated GaN. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 358-361.	0.6	27
141	Indium kinetics during the plasma-assisted molecular beam epitaxy of semipolar (11âˆ’22) InGaN layers. Applied Physics Letters, 2010, 96, 181907.	1.5	27
142	Colossal dielectric constant of poly- and single-crystalline CaCu3Ti4O12 fibres grown by the laser floating zone technique. Acta Materialia, 2011, 59, 102-111.	3.8	27
143	The photoluminescence/excitation (PL/E) spectroscopy of Eu-implanted GaN. Optical Materials, 2011, 33, 1063-1065.	1.7	27
144	Analysis of multifunctional titanium oxycarbide films as a function of oxygen addition. Surface and Coatings Technology, 2012, 206, 2525-2534.	2.2	27

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145	Ag:TiNâ€Coated Polyurethane for Dry Biopotential Electrodes: From Polymer Plasma Interface Activation to the First EEG Measurements. Plasma Processes and Polymers, 2016, 13, 341-354.	1.6	27
146	Lattice site and photoluminescence of erbium implanted in Î±â€"Al₂O₃. Journal of Materials Research, 1997, 12, 1401-1404.	1.2	26
147	Ion beam and photoluminescence studies of Er and O implanted GaN. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 383-387.	0.6	26
148	Resonant Raman scattering in ZnO:Mn and ZnO:Mn:Al thin films grown by RF sputtering. Journal of Physics Condensed Matter, 2011, 23, 334205.	0.7	26
149	Experience on divertor fuel retention after two ITER-Like Wall campaigns. Physica Scripta, 2017, T170, 014063.	1.2	26
150	Doping Î²-Ga₂O₃ with europium: influence of the implantation and annealing temperature. Journal Physics D: Applied Physics, 2017, 50, 325101.	1.3	26
151	Compositional analysis by RBS, XPS and EDX of ZnO:Al,Bi and ZnO:Ga,Bi thin films deposited by d.c. magnetron sputtering. Vacuum, 2019, 161, 268-275.	1.6	26
152	Unravelling the secrets of the resistance of GaN to strongly ionising radiation. Communications Physics, 2021, 4, .	2.0	26
153	Luminescence and structural studies of iron implanted Î±-Al2O3. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 638-643.	0.6	25
154	Up conversion from visible to ultraviolet in bulk ZnO implanted with Tm ions. Applied Physics Letters, 2005, 87, 192108.	1.5	25
155	A green-emitting CdSe/poly(butyl acrylate) nanocomposite. Nanotechnology, 2005, 16, 1969-1973.	1.3	25
156	Stability and luminescence studies of Tm and Er implanted ZnO single crystals. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 580-584.	0.6	25
157	Optical and structural analysis of bulk ZnO samples undoped and rare earth doped by ion implantation. Superlattices and Microstructures, 2006, 39, 202-210.	1.4	25
158	Raman and XRD studies of Ge nanocrystals in alumina films grown by RF-magnetron sputtering. Vacuum, 2008, 82, 1466-1469.	1.6	25
159	Fuel inventory and deposition in castellated structures in JET-ILW. Nuclear Fusion, 2017, 57, 066027.	1.6	25
160	Fe ion implantation in GaN: Damage, annealing, and lattice site location. Journal of Applied Physics, 2001, 90, 81-86.	1.1	24
161	Microstructural studies of PZT thick films on Cu foils. Acta Materialia, 2006, 54, 3211-3220.	3.8	24
162	Structural and electrical properties of Al doped ZnO thin films deposited at room temperature on poly(vinilidene fluoride) substrates. Thin Solid Films, 2009, 517, 6290-6293.	0.8	24

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163	ZrO_{<i>x</i>}N_{<i>y</i>}decorative thin films prepared by the reactive gas pulsing process. Journal Physics D: Applied Physics, 2009, 42, 195501.	1.3	24
164	Comparison of radiation detector performance for different metal contacts on CdZnTe deposited by electroless deposition method. Crystal Research and Technology, 2011, 46, 1131-1136.	0.6	24
165	Electrical properties of AlNxOy thin films prepared by reactive magnetron sputtering. Thin Solid Films, 2012, 520, 6709-6717.	0.8	24
166	Influence of stoichiometry and structure on the optical properties of AlN_xO_y films. Journal Physics D: Applied Physics, 2013, 46, 015305.	1.3	24
167	Determination of the 9Be(3He,pi)11B (i=0,1,2,3) cross section at 135Â° in the energy range 1â€"2.5MeV. Nuclear Instruments & Methods in Physics Research B, 2015, 346, 21-25.	0.6	24
168	Thin films composed of Au nanoparticles embedded in AlN: Influence of metal concentration and thermal annealing on the LSPR band. Vacuum, 2018, 157, 414-421.	1.6	24
169	First mirror test in JET for ITER: Complete overview after three ILW campaigns. Nuclear Materials and Energy, 2019, 19, 59-66.	0.6	24
170	Photoelectrochemical Water Splitting: Thermal Annealing Challenges on Hematite Nanowires. Journal of Physical Chemistry C, 2020, 124, 12897-12911.	1.5	24
171	Structural and magnetic studies of Fe-implanted Î±-Al2O3. Surface and Coatings Technology, 2000, 128-129, 434-439.	2.2	23
172	Conductivity behaviour of Cr implanted TiO2. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 158-162.	0.6	23
173	Lattice site and stability of implanted Ag in ZnO. Physica B: Condensed Matter, 2003, 340-342, 240-244.	1.3	23
174	Detection angle resolved PIXE and the equivalent depth concept for thin film characterization. X-Ray Spectrometry, 2005, 34, 372-375.	0.9	23
175	Optical doping of AlN by rare earth implantation. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 307-310.	0.6	23
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